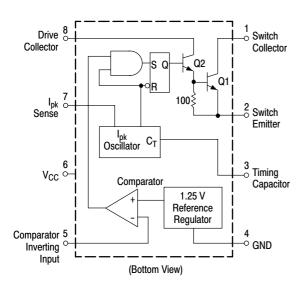
1.5 A, Step-Up/Down/ Inverting Switching Regulators

The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step-Down and Step-Up and Voltage-Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

Features

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- Pb-Free Packages are Available



This device contains 51 active transistors.

Figure 1. Representative Schematic Diagram



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

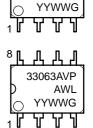


SOIC-8 D SUFFIX CASE 751





PDIP-8 P, P1 SUFFIX CASE 626



3x063AP1

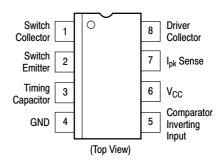
AWL

x = 3 or 4

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	40	Vdc
Comparator Input Voltage Range	V_{IR}	-0.3 to +40	Vdc
Switch Collector Voltage	V _{C(switch)}	40	Vdc
Switch Emitter Voltage (V _{Pin 1} = 40 V)	V _{E(switch)}	40	Vdc
Switch Collector to Emitter Voltage	V _{CE(switch)}	40	Vdc
Driver Collector Voltage	V _{C(driver)}	40	Vdc
Driver Collector Current (Note 1)	I _{C(driver)}	100	mA
Switch Current	I _{SW}	1.5	А
Power Dissipation and Thermal Characteristics			
Plastic Package, P, P1 Suffix			
T _A = 25°C	P _D	1.25	W
Thermal Resistance	$R_{ heta JA}$	100	°C/W
SOIC Package, D Suffix			
$T_A = 25^{\circ}C$	P_{D}	625	mW
Thermal Resistance	$R_{ heta JA}$	160	°C/W
Operating Junction Temperature	TJ	+150	°C
Operating Ambient Temperature Range	T _A		°C
MC34063A		0 to +70	
MC33063AV, NCV33063A		-40 to +125	
MC33063A		-40 to +85	
Storage Temperature Range	T _{stg}	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- Maximum package power dissipation limits must be observed.
 This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL-STD-883, Method 3015. Machine Model Method 400 V.
- 3. NCV prefix is for automotive and other applications requiring site and change control.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ V}$, $T_A = T_{low}$ to T_{high} [Note 4], unless otherwise specified.)

Characteristics	Symbol	Min	Тур	Max	Unit
OSCILLATOR	-				
Frequency (V _{Pin 5} = 0 V, C _T = 1.0 nF, T _A = 25°C)	f _{osc}	24	33	42	kHz
Charge Current (V _{CC} = 5.0 V to 40 V, T _A = 25°C)	I _{chg}	24	35	42	μΑ
Discharge Current (V _{CC} = 5.0 V to 40 V, T _A = 25°C)	I _{dischg}	140	220	260	μΑ
Discharge to Charge Current Ratio (Pin 7 to V _{CC} , T _A = 25°C)	I _{dischg} /I _{chg}	5.2	6.5	7.5	-
Current Limit Sense Voltage (I _{chg} = I _{dischg} , T _A = 25°C)	V _{ipk(sense)}	250	300	350	mV
OUTPUT SWITCH (Note 5)					
Saturation Voltage, Darlington Connection (I _{SW} = 1.0 A, Pins 1, 8 connected)	V _{CE(sat)}	-	1.0	1.3	V
Saturation Voltage (Note 6) (I _{SW} = 1.0 A, R _{Pin 8} = 82 Ω to V _{CC} , Forced $\beta \simeq 20$)	V _{CE(sat)}	-	0.45	0.7	V
DC Current Gain (I_{SW} = 1.0 A, V_{CE} = 5.0 V, T_A = 25°C)	h _{FE}	50	75	_	-
Collector Off–State Current (V _{CE} = 40 V)	I _{C(off)}	_	0.01	100	μΑ
COMPARATOR					
Threshold Voltage $T_{A} = 25^{\circ}C$ $T_{A} = T_{low} \text{ to } T_{high}$	V _{th}	1.225 1.21	1.25 -	1.275 1.29	V
Threshold Voltage Line Regulation (V _{CC} = 3.0 V to 40 V) MC33063A, MC34063A MC33063AV, NCV33063A	Reg _{line}	- -	1.4 1.4	5.0 6.0	mV
Input Bias Current (V _{in} = 0 V)	I _{IB}	-	-20	-400	nA
TOTAL DEVICE	-	-	-		
Supply Current (V_{CC} = 5.0 V to 40 V, C_T = 1.0 nF, Pin 7 = V_{CC} , $V_{Pin 5}$ > V_{th} , Pin 2 = GND, remaining pins open)	I _{CC}	-	-	4.0	mA

Forced
$$\beta$$
 of output switch :
$$\frac{IC \text{ output}}{I_C \text{ driver} - 7.0 \text{ mA}^*} \ge 10$$

 ^{4.} T_{low} = 0°C for MC34063A, -40°C for MC33063A, AV, NCV33063A
 T_{high} = +70°C for MC34063A, +85°C for MC33063A, +125°C for MC33063AV, NCV33063A
 5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

^{6.} If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 μ s for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

^{*} The 100 Ω resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.

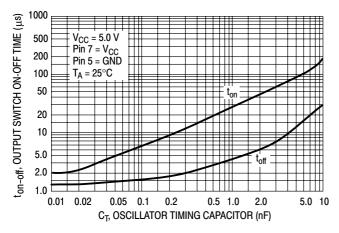


Figure 2. Output Switch On-Off Time versus Oscillator Timing Capacitor

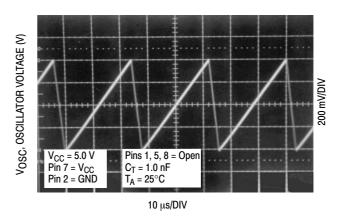


Figure 3. Timing Capacitor Waveform

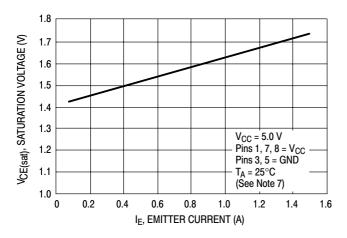


Figure 4. Emitter Follower Configuration Output Saturation Voltage versus Emitter Current

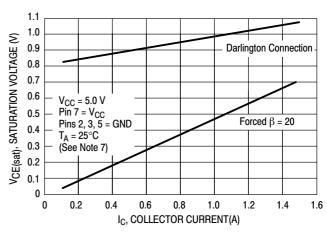


Figure 5. Common Emitter Configuration Output Switch Saturation Voltage versus Collector Current

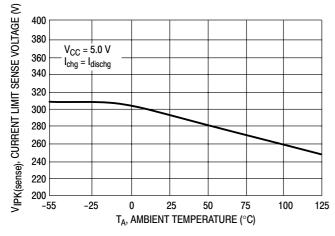


Figure 6. Current Limit Sense Voltage versus Temperature

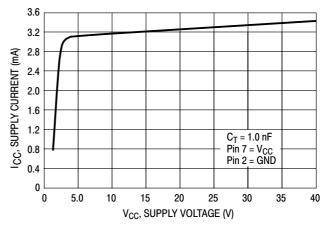
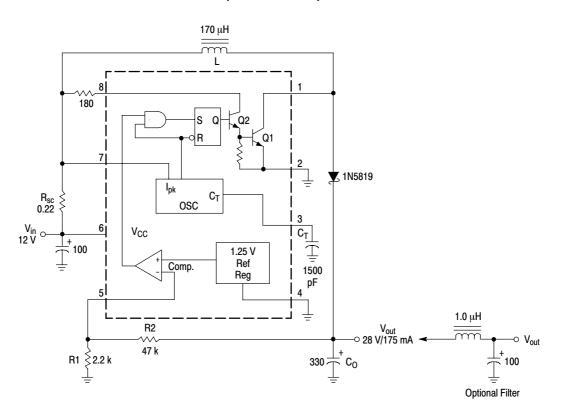


Figure 7. Standby Supply Current versus Supply Voltage

7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



Test	Conditions	Results
Line Regulation	$V_{in} = 8.0 \text{ V to } 16 \text{ V}, I_{O} = 175 \text{ mA}$	$30 \text{ mV} = \pm 0.05\%$
Load Regulation	$V_{in} = 12 \text{ V}, I_{O} = 75 \text{ mA to } 175 \text{ mA}$	10 mV = ±0.017%
Output Ripple	V _{in} = 12 V, I _O = 175 mA	400 mVpp
Efficiency	V _{in} = 12 V, I _O = 175 mA	87.7%
Output Ripple With Optional Filter	V _{in} = 12 V, I _O = 175 mA	40 mVpp

Figure 8. Step-Up Converter

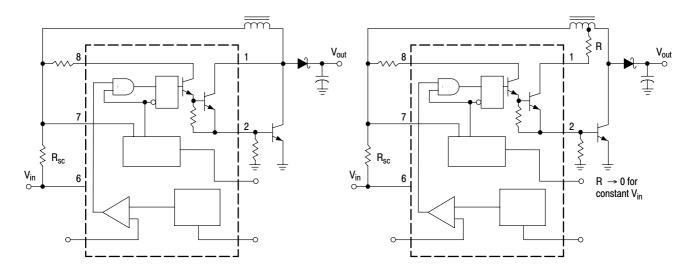


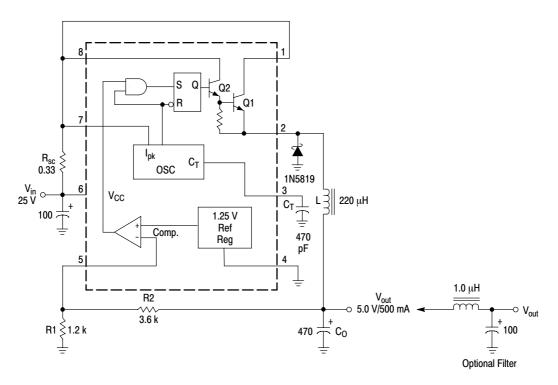
Figure 9. External Current Boost Connections for I_C Peak Greater than 1.5 A

9a. External NPN Switch

9b. External NPN Saturated Switch

(See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 μs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.



Test	Conditions	Results
Line Regulation	V _{in} = 15 V to 25 V, I _O = 500 mA	12 mV = ±0.12%
Load Regulation	V_{in} = 25 V, I_O = 50 mA to 500 mA	$3.0 \text{ mV} = \pm 0.03\%$
Output Ripple	V _{in} = 25 V, I _O = 500 mA	120 mVpp
Short Circuit Current	V_{in} = 25 V, R_L = 0.1 Ω	1.1 A
Efficiency	V _{in} = 25 V, I _O = 500 mA	83.7%
Output Ripple With Optional Filter	V _{in} = 25 V, I _O = 500 mA	40 mVpp

Figure 10. Step-Down Converter

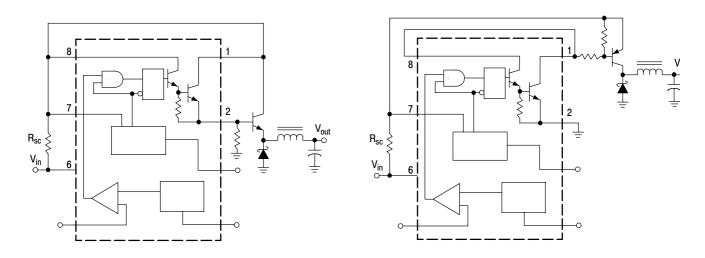
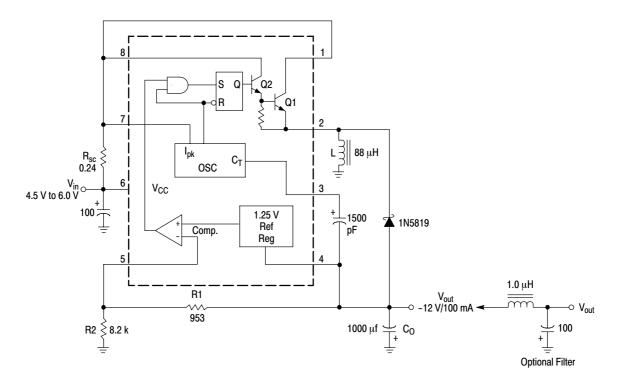


Figure 11. External Current Boost Connections for I_C Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch



Test	Conditions	Results
Line Regulation	$V_{in} = 4.5 \text{ V to } 6.0 \text{ V}, I_{O} = 100 \text{ mA}$	$3.0 \text{ mV} = \pm 0.012\%$
Load Regulation	$V_{in} = 5.0 \text{ V}, I_O = 10 \text{ mA to } 100 \text{ mA}$	$0.022 \text{ V} = \pm 0.09\%$
Output Ripple	V _{in} = 5.0 V, I _O = 100 mA	500 mVpp
Short Circuit Current	$V_{in} = 5.0 \text{ V}, R_L = 0.1 \Omega$	910 mA
Efficiency	V _{in} = 5.0 V, I _O = 100 mA	62.2%
Output Ripple With Optional Filter	$V_{in} = 5.0 \text{ V}, I_{O} = 100 \text{ mA}$	70 mVpp

Figure 12. Voltage Inverting Converter

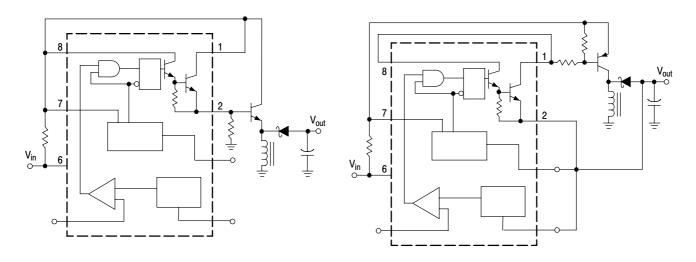
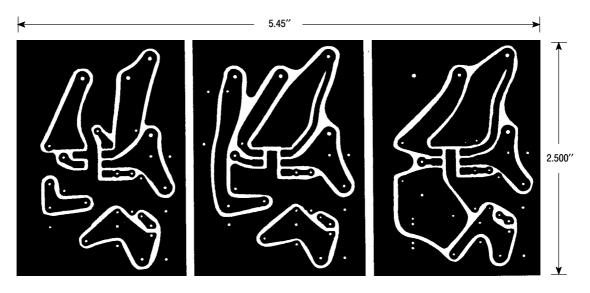


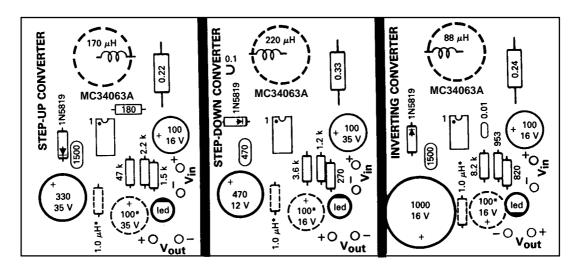
Figure 13. External Current Boost Connections for I_C Peak Greater than 1.5 A

13a. External NPN Switch

13b. External PNP Saturated Switch



(Top view, copper foil as seen through the board from the component side)



(Top View, Component Side)

*Optional Filter.

Figure 14. Printed Circuit Board and Component Layout

(Circuits of Figures 8, 10, 12)

INDUCTOR DATA

Converter	Inductance (μH)	Turns/Wire
Step-Up	170	38 Turns of #22 AWG
Step-Down	220	48 Turns of #22 AWG
Voltage-Inverting	88	28 Turns of #22 AWG

All inductors are wound on Magnetics Inc. 55117 toroidal core.

Calculation	Step-Up	Step-Down	Voltage-Inverting
t _{on} /t _{off}	$\frac{V_{\text{out}} + V_{\text{F}} - V_{\text{in(min)}}}{V_{\text{in(min)}} - V_{\text{sat}}}$	$\frac{V_{\text{out}} + V_{\text{F}}}{V_{\text{in(min)}} - V_{\text{sat}} - V_{\text{out}}}$	$\frac{ V_{\text{out}} + V_{\text{F}}}{V_{\text{in}} - V_{\text{sat}}}$
(t _{on} + t _{off})	1 f	<u>1</u> f	<u>1</u> f
t _{off}	$\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}} + 1}$	$\frac{\frac{t_{\text{on}} + t_{\text{off}}}{t_{\text{off}}}}{\frac{t_{\text{on}}}{t_{\text{off}}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{t_{on}}}{\frac{t_{on}}{t_{off}} + 1}$
t _{on}	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$
C _T	4.0 x 10 ⁻⁵ t _{on}	$4.0 \times 10^{-5} t_{on}$	$4.0 \times 10^{-5} t_{on}$
I _{pk(switch)}	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$	^{2I} out(max)	$2l_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1\right)$
R _{sc}	0.3/l _{pk(switch)}	0.3/I _{pk(switch)}	0.3/I _{pk(switch)}
L _(min)	$\left(\frac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}}\right)^{t} on(max)$	$\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}} - V_{\text{out}})}{I_{\text{pk(switch)}}}\right) t_{\text{on(max)}}$	$\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}})}{I_{\text{pk(switch)}}}\right)^{t_{\text{on(max)}}}$
C _O	9 $\frac{I_{out}^{t_{on}}}{V_{ripple(pp)}}$	$\frac{I_{pk(switch)}^{(t_{on} + t_{off})}}{8V_{ripple(pp)}}$	$9 \frac{I_{out}^{t_{on}}}{V_{ripple(pp)}}$

 V_{sat} = Saturation voltage of the output switch.

The following power supply characteristics must be chosen:

V_{in} - Nominal input voltage.

 V_{in} – Nominal input voltage. V_{out} – Desired output voltage, $|V_{out}| = 1.25 \left(1 + \frac{R2}{R1}\right)$ I_{out} – Desired output current. I_{min} – Minimum desired output switching frequency at the selected values of V_{in} and I_{O} .

NOTE: For further information refer to Application Note AN920A/D and AN954/D.

Figure 15. Design Formula Table

 V_F = Forward voltage drop of the output rectifier.

 $V_{ripple(pp)}$ – Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

ORDERING INFORMATION

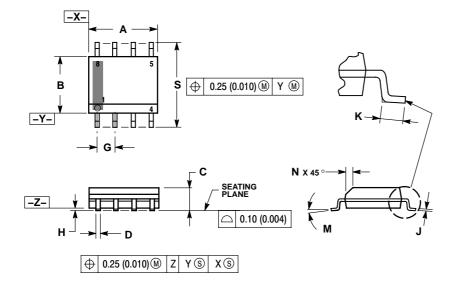
Device	Package	Shipping [†]
MC33063AD	SOIC-8	98 Units / Rail
MC33063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063ADR2	SOIC-8	2500 Units / Tape & Reel
MC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33063AP1	PDIP-8	50 Units / Rail
MC33063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail
MC33063AVD	SOIC-8	98 Units / Rail
MC33063AVDG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063AVDR2	SOIC-8	
MC33063AVDR2G	SOIC-8 (Pb-Free)	
NCV33063AVDR2*	SOIC-8	2500 Units / Tape & Reel
NCV33063AVDR2G*	SOIC-8 (Pb-Free)	
MC33063AVP	PDIP-8	50 Units / Rail
MC33063AVPG	PDIP-8 (Pb-Free)	50 Units / Rail
MC34063AD	SOIC-8	98 Units / Rail
MC34063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC34063ADR2	SOIC-8	2500 Units / Tape & Reel
MC34063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC34063AP1	PDIP-8	50 Units / Rail
MC34063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*NCV33063A: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

PACKAGE DIMENSIONS

SOIC-8 NB **D SUFFIX** CASE 751-07 **ISSUE AG**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

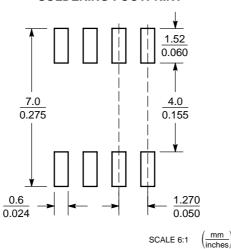
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- 4. MAXIMUM MOLD PROTRUSION 0.13 (0.000)
 PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT
- MAXIMUM MATERIAL CONDITION. 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
Ν	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

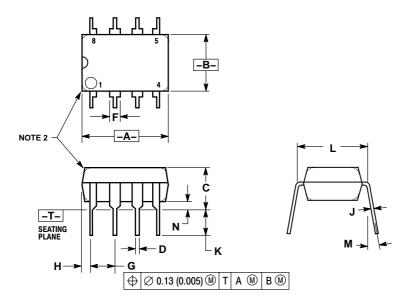
SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

PDIP-8 P, P1 SUFFIX CASE 626-05 ISSUE L



NOTES:

- DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300	BSC
M		10°		10°
N	0.76	1.01	0.030	0.040

SENSEFET is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.